PrintedPage:01 SubCoo						bCod	e: KF	EC 0'	77	
Paper		RollNo:								
	N	BTECH I) THEORY EXAMI MICRO & SMART S			2-23					
	3Hours					Total	Mar	ks:10)0	
Note:	1. AttemptallSections. If r	require any missing da	ata; then ch	noose	suital	oly.				
	2. Any special paper spec	ific instruction. SECTIONA								
1.	Attempt all questions i	n brief.					2x	10= 2	20	
(b) (c) (d) (e) (f) (g) (h) (i)	What is the difference bet Whatdoyoumeanbysmart and Which transducer is known Explainmicromachining power what is dynamic range? Write the applications of power what is the use of Hall Eff What is the difference bet Define intelligent sensor. Attempt any three of the Explain in detail Silicon Whatarethegoalsand ap What are smart-mater systems. Explain Micro machinareas. Describeand salient fear	systems? mart materials andMicro as 'self-generating to process. piezo-resistive pressurfect sensors? ween tactile and non-to SECTIONB ne following: ncapacitive acceleromophicationsofintegrated ial systems? Evolutioned transducers. Evolutioned transducers.	re sensor? tactile sensor d Microsys on of sma	sor? tem? art m	o-mar		ructur	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	nd	ations
3.	Attempt any one part of	of the following:		.,			102	x1=1	0	
(a) (b)	Describepiezoelectric i Discuss in detail about J	piezo-resistive pressur			S.					
4.	Attempt any one part of	of the following:					102	x1=1	0	
(a) (b) 5.	Writeashort noteonadva ExplaintheEmerging tro Attempt any one part of	endsSilicon wafer pro	_	on			102	x1=1	0	
(a) (b)	Describe Poisson effect Explainmodeling of co				ıs.					

What is residual stress and stress gradients? Give difference between them.

Explain integration of Microsystemsand microelectronics.

Attempt any one part of the following:

Attempt any one part of the following:

6.

(a)

(b) 7.

10x1=10

10x1=10